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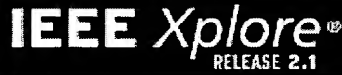
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 Shibata, N.; Morimura, H.; Watanabe, M.;  
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- ☐ 2. **Reliability degradation of high density DRAM cell transistor j leakage current induced by band-to-defect tunneling under tl bias-temperature stress**  
 Young Pil Kim; Young Wook Park; Joo Tae Moon; Kim, S.U.;  
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- ☐ 3. **Gate-Length Biasing for Runtime Leakage**  
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- ☒ 6. **Experimental and theoretical investigation of nonvolatile memory retention**  
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